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CJFET Differential Pairs Constructions and Characteristics for Design of CBiCJFet Differential Amplifiers and Differential Difference Amplifiers

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We have developed technology and construction solutions system to increase differential pairs (DP) of JFet with p- and n-channels identity, which are included into silicon complementary bipolar process of SPE "Pulsar" (Moscow). The possibility of creating several types of JFet DPs within the process is shown. The paper presents the results of experimental studies of two types of DP JFet designs with p- and n-channels for the spread of gate-source voltage ΔV_{GS} depending on the drain current and drain-source voltage.

The main features of the first design of p-channel JFets were the following: formation of drain/source area due to passive base of npn-transistor and deep collector areas for pnp-transistor; channel formation based on p-layer collector of pnp-transistor; formation of bottom gate using p^+ buried layer; top gate formation due to active base and polysilicon emitter of npn-transistor. A feature of the second JFet design was top gate formation due to passive base. The designs of the first and second types of n-channel Jfet were formed similarly, taking into account the replacement of the applied areas of bipolar transistors with opposite ones in the type of conductivity.

It was found that with increasing drain current ΔV_{GS} decreases, and with increasing drain-source voltage ΔV_{GS} at high currents increases for DP based on p-channel JFet with the first type of design. The maximum difference ΔV_{GS} was in the range of 5–80 mV for a given differential pair JFet with a p-channel. On plots for DP p-channel JFet with the second type design a significantly lower voltage spread ΔV_{GS} was shown: for example, for the drain current $I_D = 50\ \mu A$ the voltage spread ΔV_{GS} did not exceed 10 mV. In this case the voltage spread ΔV_{GS} practially did not depend on drain-source voltage in contrast to differenctial pair of the first type.

The second type JFet n-channel differential pairs like for the DP p-channel JFet provided lower spread values in comparison with the first type design: ΔV_{GS} reached values of 5-20 mV. Moreover, for the design of the second type, a significantly weaker effect of the drain-source voltage on ΔV_{GS} was observed at high current densities. The developed designs of differential pairs based on p- and n-channel JFet are recommended for use in organizing the production of CBiCJFet analog circuits, including operations at low temperatures.

Key words: p-n junction field-effect transistors; differential pair; drain-gate characteristic; silicone complementary bipolar technology

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Introduction

An identity of JFet differential pair (DP) at similar source currents is an important parameter, which characterizes a quality of JFet construction and corresponding JFet process [1–9]. This DP's property significantly influences zero-level of analog ICs, including operational [10–12] and instrumental [13] amplifiers, as well as errors of input low-noise [14–16], charge-sensitive [17, 18] and transimpedance [19] amplifiers, sources of reference current and voltage [20] and so on is a priority in the design of AM.

A process, developed by SPE "Pulsar" [21], allows to design analog ICs, containing JFets and HF complementary bipolar transistors. But bipolar active elements (especially p-n-p) have extremely low values of base current gain in cryogenic temperatures range. So to build low-temperature and low noise sensor interfaces and input stage of corresponding special analog ICs it is appropriate to implement only on

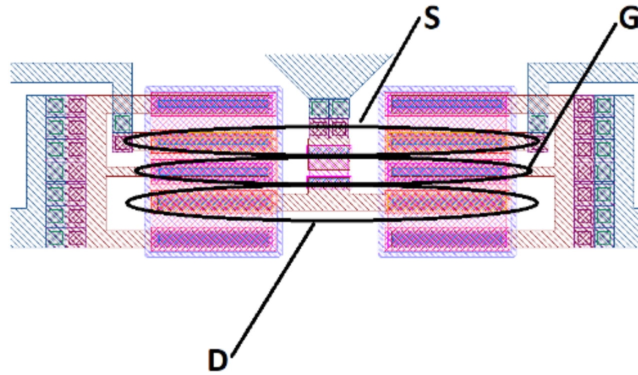

Fig. 1. p-Channel JFets Differential Pair Topology

CJFet components. This limitation causes development problem for analog ICs' functional unit base CJFet, on base of which it is possible to develop different OA, continuously operating voltage stabilizers, current and voltage comparators, active ARC etc. Todays' level of CJFet's circuitry is very low and not developed. It causes a problem of CJFet analog OM circuitry, it is more compliacated than the one for CMOS and BJ processes. Its reason is different static voltage polarity between source and gate of JFet in active mode (comparing with drain-source polarity). As a consequence the following is required firstly to design CJFet analog OM: special CJFet current mirrors (CM), which are not implemented per circuits traditional for CMOS and BJT, CJFet input differential stages, buffer amplifiers (BA) with source output, rail-to-rail CJFet BA, input stages of fast CJFet AM, intermediate folded cascode, static mode stabilizer circuit (reference current sources and potential offset circuit), operational amplifiers with increased gain, fast CJFet OA, micropower CJFet OA, differential difference amplifier, OTA amplifiers with controled slope etc. Conceptually we need updated concept for developing wide class of analog CJFet ICs, which practically were not developed because of dominant impact of cheap techology for CMOS and BJ and small production of low temperature microelectronic devices. However modern necessities of space instrumentation, high energy physics, medicine, quantum computing systems, high speed railway transport etc. stimulate development of this scientific direction. The above circuitry tasks are of high priority.

The methods to increase identity of JFet DP are connected with JFet rational construction and its implementation technology [21]. It is known that CBi-pCJFet process in BiCom3HV modification of Texas Instruments company [22, 23] allows developing new precision operational amplifiers OPA211 and OPA827 wth JFet and BJT, which combine ultralow level of noise coefficient and low power consumtion. The said amplifiers are characterized by enabling parameters. BiCom3HV process makes possible to provide next generation of analog electronic component base, it includes all best microelectronic achievements. But OPA211 and OPA827 operate at temperatures of -40^{0}C and higher according to BiCom3HV process, which is provided by bipolar transistors application. It is not enough for several tasks.

The purpose of this article is to develop and describe process and construction solutions, which provide identity improvement for CJFet DP with p- and n-channels, integrated into silicon complementary bipolar technological process of SPE “Puslar” (Moscow).

1 p-Channel JFet Differential Pairs mady by SPE “Pulsar” and their Basic Characteristics

It is possible to develop several types of p-n-junction field-effect transistors (JFet) within silicon-based bipolar process. There is a topology of differential pair of n-channel JFets on Fig. 1. It includes the following sections: S-area — source, G-area — top gate, D-area — drain.

The parameters of the first construction of p-channel JFets (Type 1) are the following:

- development of drain/source area due to passive base of npn-transistor and deep collector areas for pnp-transistor, when a distance between drain/souce areas are 4.2 μm;
- channel development based on p-layer collector of pnp-transistor;
- development of bottom gate using p+ buried layer;
- top gate development due to active base and polysilicon emitter of npn-transistor.

There are drain-gate characteristics of p-channel JFets differential pair at 5 V and 10 V of drain voltage.

A dependence of drain-source voltage nonidentity ΔV_{GS} from drain current is defined for the above contruction of p-channel JFets (Fig. 3). The Fig. 3 shows that ΔV_{GS} reduces when current increases, and ΔV_{GS} increases at high currents, when drain-source voltage increases. A spread of voltages ΔV_{GS} does not go below 80 mV in a drain current rage up to 50 μA.

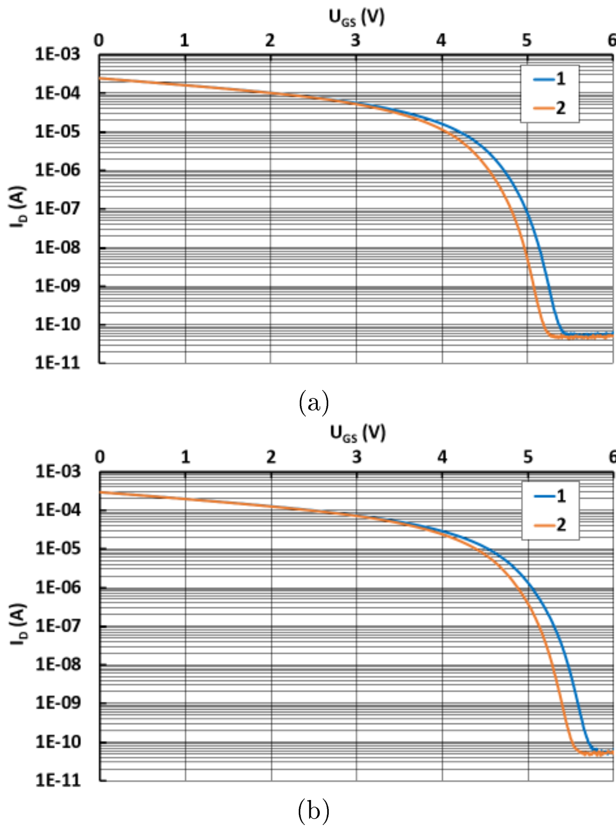

Fig. 2. Dependence $I_D = f(U_{GS})$ at $U_{DS} = 5$ V (a) and $U_{DS} = 10$ V (b) for p-Channel JFet Differential Pair (Type 1)

The parameters of p-channel JFET second construction (Type 2) are the following:

- development of drain/source area due to passive base of npn-transistor and deep collector areas for pnp-transistor, when a distance between drain/souce areas are 6.6 μm;
- channel development based on p-layer collector of pnp-transistor;
- development of bottom gate using p+ buried layer;
- top gate development due to passive base.

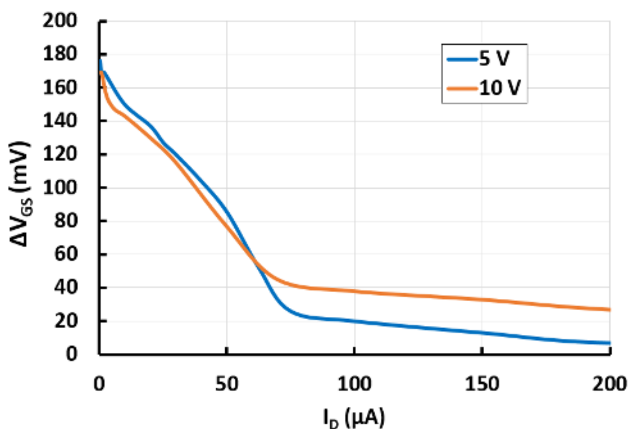

Fig. 3. Dependence $\Delta V_{GS} = f(I_D)$ at $U_{DS} = 5$ and 10 V for p-Channel JFET Differential Pair (Type 1)

There are drain-gate characteristics of second type p-channel JFets differential pair at 5 V and 10 V on drain.

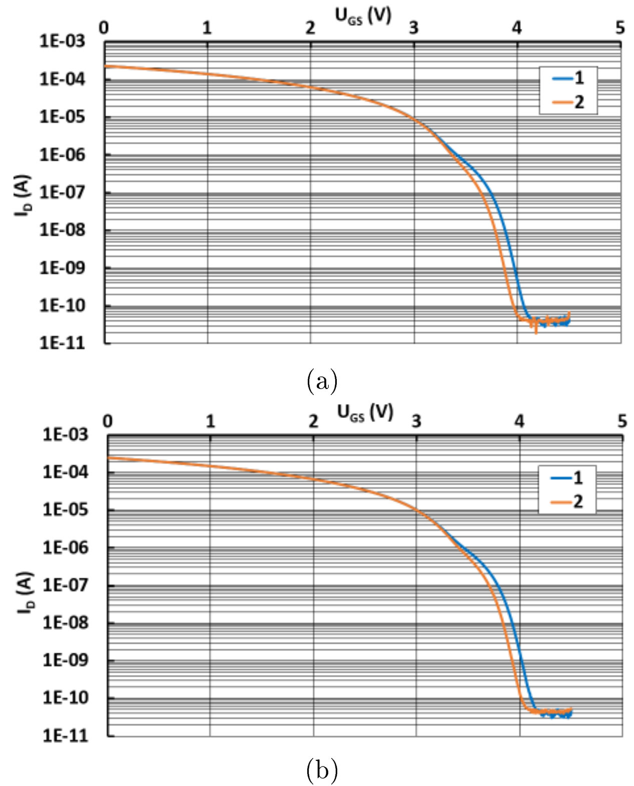

Fig. 4. Dependence $I_D = f(U_{GS})$ at $U_{DS} = 5$ V (a) and $U_{DS} = 10$ V (b) for p-Channel JFet Differential Pair

There is a dependence of drain-source ΔV_{GS} voltage spread on drain current for this pair of transistors.

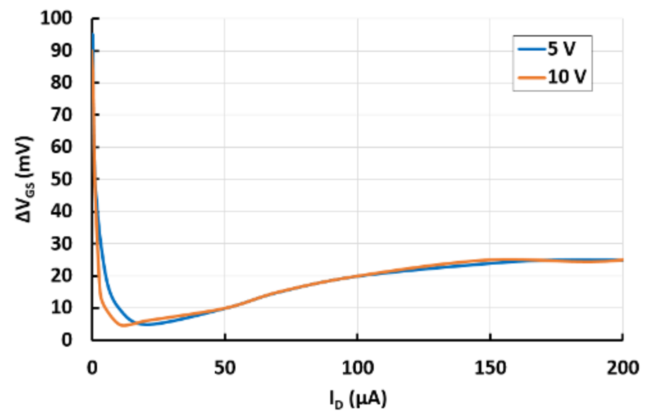

Fig. 5. Dependence $\Delta V_{GS} = f(I_D)$ at $U_{DS} = 5$ V and 10 V for p-Channel JFET Differenctial Pair (Type 2)

The Fig. 5 shows that the second type JFet differential pair has significantly smaller spread of voltages ΔV_{GS}. For example, a voltage spread ΔV_{GS} does not exceed 10 μV for drain current $I_D = 50$ μA. In this case the voltage spread ΔV_{GS} practially does not depend on drain-source voltage in contrast to differenctial pair of the first type.

2 n-Channel JFet Differential Pairs made by SPE "Pulsar" and Their Basic Characteristics

There is a topology of n-channel Fets differential pair on Fig. 6. It includes the following sections: S-area - source, G-area — top gate, D-area — drain.

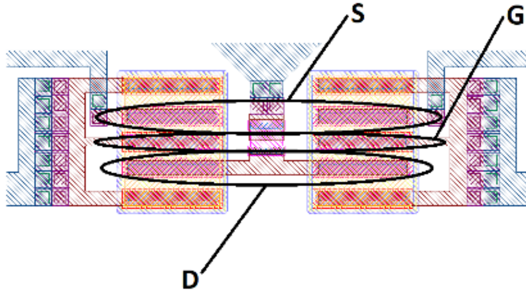

Fig. 6. n-Channel JFets Differential Pair Topology

We investigated two types of n-channel JFets similarly to p-channel JFets: Tyep 1 — top gate area based on active base of npn-transistors, Type 2 — top gate area is developed based on passive base of npn-transistors.

There are drain-gate charactrisitics of n-channel JFets at 5 V and 10 V on drain for differential pairs of the first and second types on Fig. 7 and 8 correspondently.

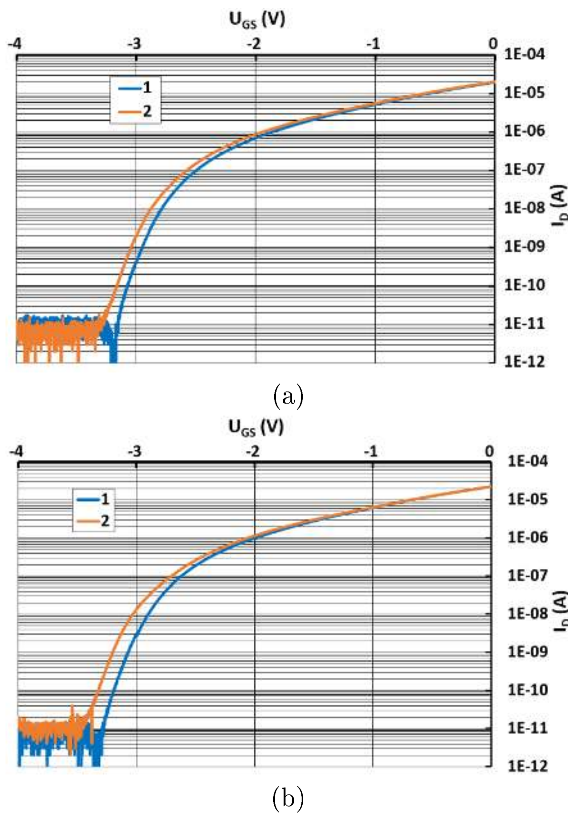

Fig. 7. Dependence $I_D = f(U_{GS})$ at $U_{DS} = 5$ V (a) and 10 V (b) for n-Channel JFET Differential Pair (Type 1)

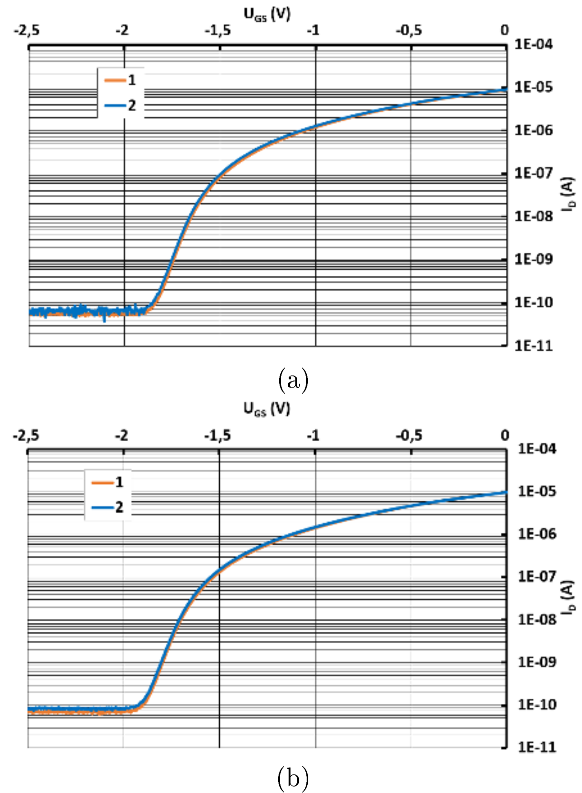

Fig. 8. Dependence $I_D = f(U_{GS})$ at $U_{DS} = 5$ V (a) and 10 V (b) for n-Channel JFET Differential Pair (Type 2)

A cut-off voltage is U_{T0} $\tilde{3}$.2-1.7 V for n-channel transistors in comparison with U_{T0} $\tilde{5}$.5-4 V for p-channel transistors. As a result there are smaller current of drain for n-channel JFet at similar area. Thus it is reasonable to compare these transistors at drain current of 10 μA, but not at 50 μA (as was done for p-channel transistors).

Dependence ΔV_{GS} on drain current (Fig. 9) for the first type n-channel transistors differential pair substantially similar to the difference of the first type p-channel JFet differential pair (Fig. 3). But there is significantly weaker influence of drain-source voltage for n-channel JFet at higher current density. ΔV_{GS} for drain current $I_D = 10$ mA does not exceed 30 mV.

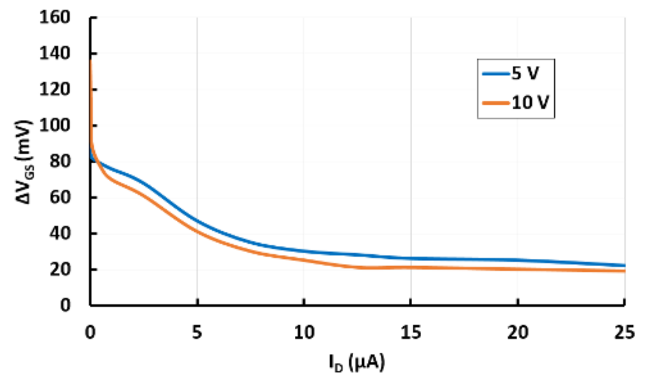

Fig. 9. Dependence $\Delta V_{GS} = f(I_D)$ at $U_{DS} = 5$ V and 10 V n-Channel JFET Differential Pair (Type 1)

The values of voltage spread ΔV_{GS} are significanly lower: from 5 to 21 mV for the second type n-channel transistors (Fig. 10). ΔV_{GS} is not higher than 8 mV at $I_D = 10$ μA. Similar to p-channel transistors (Type 2) there is an optimum value of drain current at which there is a minimum of ΔV_{GS}. When the drain current increases any further, ΔV_{GS} weakly depends on drain current value similarly to all considered types of differential pairs.

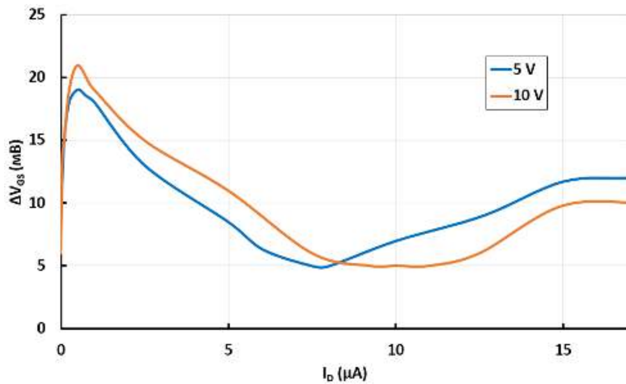

Fig. 10. Dependence $\Delta V_{GS} = f(I_D)$ at $U_{DS} = 5$ V and 10 V for n-Channel JFET Differential Pair (Type 2)

So it is defined, that to provide minimum values of spread ΔV_{GS} for JFet differential pair, including considerting low temperature influence, it is reasonalbe to use the second type of p-n junction complementary field-effect transistors construction.

Conclusion

We have developed constructions of p- and n-channel JFets, included into silicon complementary bipolar process of SPE "Pulsar", which provide relatively high identity of drain-gate characteristics at their differential input ($U_{os} \leq 5 \div 10$ mV) and possibility to develop CBiCFet integral circuits.

Acknowledgments

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Конструкції і характеристики диференціальних пар CJFet транзисторів для проектування CBiCJFet диференціальних і мультидиференціальних операційних підсилювачів

Савченко Є. М., Дроздов Д. Г., Родін В. Г., Грушин А. И., Дюканов П. О., Прокопенко М. М.

Розроблено систему технологічних і конструктивних рішень, що забезпечує підвищення ідентичності диференціальних пар (DP) польових транзисторів з керуючим p-n переходом (JFet) з p- і n-каналами, що вбудованих в кремнієвий комплементарний біполярний технологічний процес "НВП "Пульсар". Показано, що в рамках даного технологічного процесу можливе створення декількох типів DP JFet. В роботі представлені результати експериментальних досліджень двох типів конструкцій DP JFet з p- і n- каналами з розкидом напруги затвор-витік ΔV_{GS} в залежності від струму стоку і напруги стік-витік. До основних особливостей першої конструкції p-канального Jfet ставилися: формування областей стоку / витоку за рахунок пасивної бази npn-транзистора і областей глибокого колектора pnp-транзистора; формування каналу на основі p-шару колектора pnp-транзистора; формування нижнього затвору з застосуванням p^+ прихованого шару; формування верхнього затвору за рахунок активної бази і полікремнієвогох емітера npn-транзистора. Особливістю другої конструкції Jfet було формування верхнього затвору внаслідок пасивної бази. Конструкції першого і другого типів n-канальних Jfet формувалися аналогічно з урахуванням заміни застосовуваних областей біполярних транзисторів на протилежні за типом провідності. Для DP на основі p-канальних JFet з конструкцією першого типу встановлено, що зі зростанням струму стоку величина ΔV_{GS} знижується, а зі збільшенням напруги стік-витік ΔV_{GS} за великих струмах зростає. Для даної диференціальної пари JFet з p-каналом максимальна різниця ΔV_{GS} лежить в межах 5 - 80 мВ. Для DP p-канальних JFet з конструкцією другого типу наведено графіки, що показують істотно менше значення розкиду напруг ΔV_{GS}: наприклад, для значення струму стоку I_D = 50 мкА розкид напруг ΔV_{GS} не перевищує 10 мВ. При цьому, на відміну від першого типу DP, розкид напруги ΔV_{GS} практично не залежить від напруги стік-витік. Як і для DP p-канальних JFet диференціальні пари n-канальних JFet другого типу забезпечили менші значення розкиду в порівнянні з конструкцією першого типу: ΔV_{GS} досягає значень 5 - 20 мВ. Також для конструкції другого типу спостерігалося значно слабший вплив напруги стік-витік на ΔV_{GS} у разі високої щільності струму. Розроблені конструкції диференціальних пар на основі p- і n-канальних JFet рекомендується використовувати при організації виробництва CBiCJFet аналогових мікросхем, в тому числі для експлуатації в умовах низьких температур.

Ключові слова: польові транзистори з керованим p-n переходом; диференціальні пари; характеристика стік-затвор; кремнієва комплементарна біполярна технологія

Конструкции и характеристики дифференциальных пар CJFet транзисторов для проектирования CBiCJFet дифференциальных и мультидифференциальных операционных усилителей

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Разработана система технологических и конструктивных решений, обеспечивающая повышение идентичности дифференциальных пар (DP) полевых транзисторов с управляющим p-n переходом (JFet) с p- и n-каналами, встроенных в кремниевый комплементарный биполярный технологический процесс АО "НПП "Пульсар" (г. Москва). Показано, что в рамках данного технологического процесса возможно создание нескольких типов DP JFet. В работе представлены результаты экспериментальных исследований двух типов конструкций DP JFet с p- и n- каналами по разбросу напряжения затвор-исток ΔV_{GS} в зависимости от тока стока и напряжения сток-исток.

К основным особенностям первой конструкции p-канального Jfet относились: формирование областей стока/истока за счёт пассивной базы npn-транзистора и областей глубокого коллектора pnp-транзистора; формирование канала на основе p–слоя коллектора pnp-транзистора; формирование нижнего затвора с применением p^+ скрытого слоя; формирование верхнего затвора за счёт активной базы и поликремниевого эмиттера npn-транзистора. Особенностью второй конструкции Jfet являлось формирование верхнего затвора за счёт пассивной базы. Конструкции первого и второго типов n-канальных Jfet формировались аналогично с учетом замены применяемых областей биполярных транзисторов на противоположные по типу проводимости.

Для DP на основе p-канальных JFet с конструкцией первого типа установлено, что с ростом тока стока величина ΔV_{GS} снижается, а с увеличением напряжения

сток-исток ΔV_{GS} при высоких токах возрастает. Для данной дифференциальной пары JFet с p-каналом максимальная разница DVGS лежит в пределах 5 – 80 мВ. Для DP p-канальных JFet с конструкцией второго типа приведены графики, показывающие существенно меньшее значение разброса напряжений ΔV_{GS}: например, для значения тока стока $I_D = 50$ мкА разброс напряжений ΔV_{GS} не превышает 10 мВ. При этом, в отличие от первого типа DP, разброс напряжения ΔV_{GS} практически не зависит от напряжения сток-исток. Как и для DP p-канальных JFet дифференциальные пары n-канальных JFet второго типа обеспечили меньшие значения разброса в сравненни с конструкцией первого типа: ΔV_{GS} достигает значений 5 – 20 мВ. Также для конструкции второго типа наблюдалось значительно более слабое влияние напряжения сток-исток на ΔV_{GS} при высоких плотностях тока.

Разработанные конструкции дифференциальных пар на основе p- и n-канальных JFet рекомендуется использовать при организации производства CBiCJFet аналоговых микросхем, в том числе для эксплуатации в условиях низких температур.

Ключевые слова: полевые транзисторы с управляющим p-n переходом; дифференциальные пары; стоко-затворная характеристика; кремниевая комплементарная биполярная технология